Specification Amendments

Please replace paragraphs 007 beginning at page 4 with the following rewritten paragraph:

007 Typically, in a dual damascene manufacturing process known in the art as a via-first-trench last process conventional photolithographic processes using a photoresist layer ~~is~~ are first used to pattern and expose an etching mask which is used for etching via openings through the IMD layer. Subsequently a similar process is used to define trench openings that are formed substantially over the via openings which in turn define metallic interconnect lines. tThe via openingg and trench openings are subsequently filled with metal to form metalization vias and metal interconnect lines. The surface may then be planarized by conventional techniques to better define the metal interconnect lines and prepare the substrate for further processing.

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Please replace the paragraph 0042 beginning on page 18 with the following rewritten paragraph:

0042 The photoresist layer ~~36~~ 37 serving to define the trench opening pattern ~~30~~ 39 is preferably from ~~5000 to 9000~~ 1000 to 20000 Angstroms. It will further be appreciated by those skilled in the art that positive photoresist is the preferable photoresist.